RT1P44BX SERIES

(Transistor)

UNIT: mm

0.5

Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

DESCRIPTION

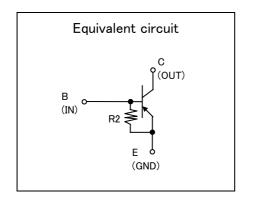
RT1P44BX is a one chip transistor with built-in bias resistor, NPN type is RT1N44BX.

FEATURE

•Built-in bias resistor (R2=47k Ω).

APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit.



OUTLINE DRAWING

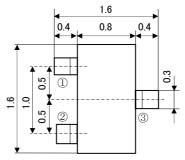
RT1P44BC

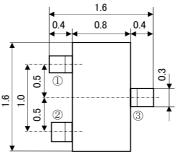
0.5

1.90

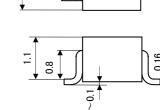
2.5

1.5





RT1P44BU



JEITA: SC-59

0 JEITA: -

JEDEC: -

Terminal Connector

3: Collector

①:Base 2: Emitter **Terminal Connector**

JEDEC: Similar to TO-236

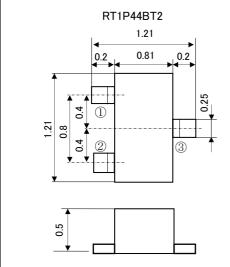
1:Base

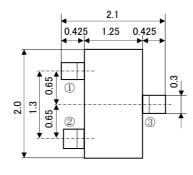
2: Emitter

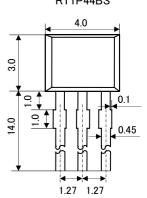
3: Collector

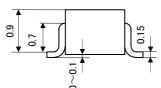
RT1P44BM

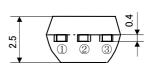
RT1P44BS











JEITA, JEDEC: -ISAHAYA: T-USM **Terminal Connecto**

1:Base

2: Emitter

3: Collector



JEDEC: -**Terminal Connector**

(1):Base

(2): Emitter

3: Collector

JEITA: -JEDEC: -

Terminal Connector

(1): Emitter

2: Collector

3:Base

www.DataSheet4U.com

RT1P44BX SERIES

(Transistor)

Transistor With Resistor
For Switching Application
Silicon PNP Epitaxial Type

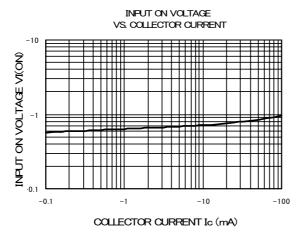
MAXIMUM RATING (Ta=25°C)

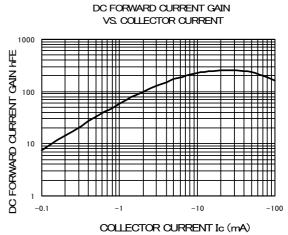
SYMBOL	PARAMETER	RATING					
		RT1P44BT2	RT1P44BU	RT1P44BM	RT1P44BC	RT1P44BS	UNIT
V _{CBO}	Collector to Base voltage	-50					
V_{EBO}	Emitter to Base voltage	-6					V
V_{CEO}	Collector to Emitter voltage	-50					
Ic	Collector current	-100					
I _{CM}	Peak Collector current	-200					mA
P _c	Collector dissipation(Ta=25°C)	125(※)	150	200		450	mW
Tj	Junction temperature	+125 +150					°C
Tstg	Storage temperature	-55 ~ +125					°C

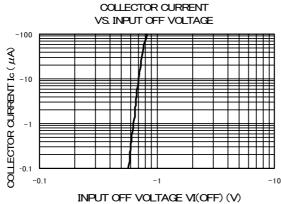
ELECTRICAL CHARACTERISTICS (Ta=25°C) (X) package mounted on 9mm × 19mm × 1mm glass-epoxy substrate.

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	I _C =-100 μ A, R _{BE} =∞	-50			V
I _{CBO}	Collector cut off current	V_{CB} =-50V, I $_{E}$ =0			-0.1	μΑ
h_{FE}	DC forward current gain	V_{CE} =-5V, I _C =-5mA	68			ı
$V_{CE(sat)}$	C to E saturation voltage	$I_{C} = -10 \text{mA}, I_{B} = -0.5 \text{mA}$			-0.3	٧
R ₂	Emitter-base resistance		33	47	61	kΩ
f_{T}	Gain band width product	V_{CE} =-6V, I_{E} =10mA	·	150		MHz

TYPICAL CHARACTERISTICS









Marketing division, Marketing planning department 6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

Keep safety first in your circuit designs!

•ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary, (2) use of non-farmable material or (3) prevention against any malfunction or mishap.

Notes regarding these materials

- •These materials are intended as a reference to our customers in the selection of the ISAHAYA products best suited to the customer's application; they don't convey any license under any intellectual property rights, or any other rights, belonging ISAHAYA or third party.
- ISAHAYA or third party.

 ISAHAYA or third party:

 ISAHAYA Electronics Corporation assumes no responsibility for any damage, or infringement of any third party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams and charts, represent information on products at the time of publication of these materials, and are subject to change by ISAHAYA Electronics Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor for the latest product information before purchasing product listed berein
- ISAHAYA Electronics Corporation products are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact ISAHAYA electronics corporation or an authorized ISAHAYA products distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- •The prior written approval of ISAHAYA Electronics Corporation is necessary to reprint or reproduce in whole or in part these
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or re-export contrary to he export control laws and regulations of Japan and/or the country of destination is prohibited.

 Please contact ISAHAYA Electronics Corporation or authorized ISAHAYA products distributor for further details on these
- •Please contact ISAHAYA Electronics Corporation or authorized ISAHAYA products distributor for further details on these materials or the products contained therein.